

## **KSA1381**

## **CRT Display, Video Output**

High Collector-Emitter Breakdown Voltage: V<sub>CEO</sub>= -300V
Low Reverse Transfer Capacitance: C<sub>re</sub>= 2.3pF at V<sub>CB</sub> = -30V



# **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

| Symbol           | Parameter                                    | Ratings    | Units |
|------------------|--|------------|-------|
| V <sub>CBO</sub> | Collector-Base Voltage                       | - 300      | V     |
| V <sub>CEO</sub> | Collector-Emitter Voltage                    | - 300      | V     |
| V <sub>EBO</sub> | Emitter-Base Voltage                         | - 5        | V     |
| I <sub>C</sub>   | Collector Current (DC)                       | - 100      | mA    |
| I <sub>CP</sub>  | Collector Current (Pulse)                    | - 200      | mA    |
| P <sub>C</sub>   | Collector Dissipation (T <sub>C</sub> =25°C) | 7          | W     |
| P <sub>C</sub>   | Collector Dissipation (T <sub>a</sub> =25°C) | 1.2        | W     |
| T <sub>J</sub>   | Junction Temperature                         | 150        | °C    |
| T <sub>STG</sub> | Storage Temperature                          | - 55 ~ 150 | °C    |

## Electrical Characteristics $T_C=25$ °C unless otherwise noted

| Symbol                | Parameter                            | Test Condition                            | Min.  | Тур. | Max.  | Units |
|-----------------------|--------------------------------------|---|-------|------|-------|-------|
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage     | $I_C = -10\mu A, I_E = 0$                 | - 300 |      |       | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | $I_C = -1 \text{mA}, I_B = 0$             | - 300 |      |       | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | $I_E = -10\mu A, I_C = 0$                 | - 5   |      |       | V     |
| I <sub>CBO</sub>      | Collector Cut-off Current            | $V_{CB} = -200V, I_{E} = 0$               |       |      | - 0.1 | μΑ    |
| I <sub>EBO</sub>      | Emitter Cut-off Current              | $V_{EB} = -4V, I_{C} = 0$                 |       |      | - 0.1 | μΑ    |
| h <sub>FE</sub>       | DC Current Gain                      | $V_{CE} = -10V, I_{C} = -10mA$            | 40    |      | 320   |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | $I_C = -20 \text{mA}, I_B = -2 \text{mA}$ |       |      | - 0.6 | V     |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage      | $I_C = -20 \text{mA}, I_B = -2 \text{mA}$ |       |      | - 1   | V     |
| f <sub>T</sub>        | Current Gain Bandwidth Product       | $V_{CE} = -30V, I_{C} = -10mA$            |       | 150  |       | MHz   |
| C <sub>ob</sub>       | Output Capacitance                   | V <sub>CB</sub> = - 30V, f = 1MHz         |       | 3.1  |       | pF    |
| C <sub>re</sub>       | Reverse Transfer Capacitance         | V <sub>CB</sub> = - 30V, f = 1MHz         |       | 2.3  |       | pF    |

## **h**<sub>FE</sub> Classification

| Classification  | С       | D        | Ш         | F         |
|-----------------|---------|----------|-----------|-----------|
| h <sub>FE</sub> | 40 ~ 80 | 60 ~ 120 | 100 ~ 200 | 160 ~ 320 |

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# **Typical Characteristics**

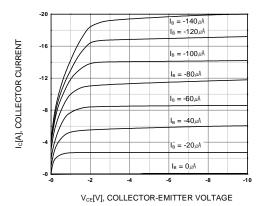


Figure 1. Static Characteristic

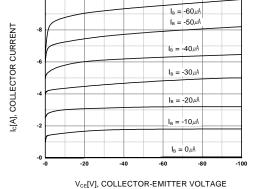


Figure 2. Static Characteristic

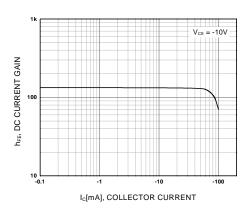


Figure 3. DC current Gain

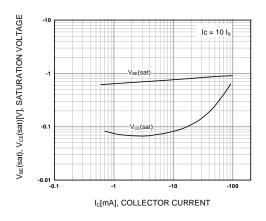


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

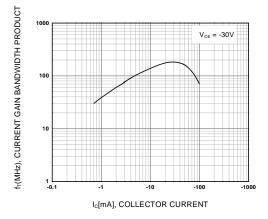


Figure 5. Current Gain Bandwidth Product

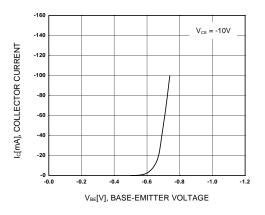


Figure 6. Base-Emitter On Voltage

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# Typical Characteristics (Continued)

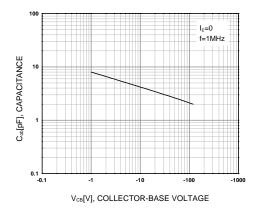


Figure 7. Collector Output Capacitance

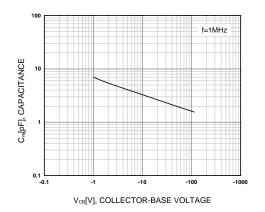


Figure 8. Reverse Transfer Capacitance

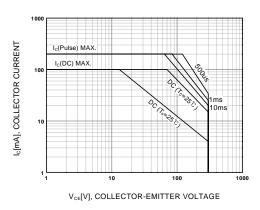


Figure 9. Safe Operating Area

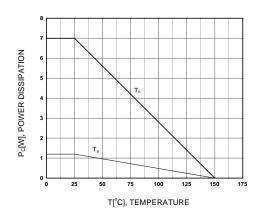
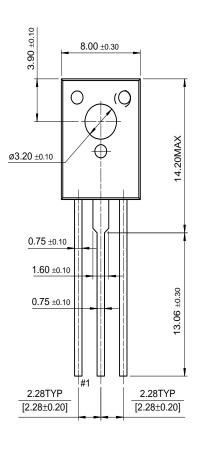


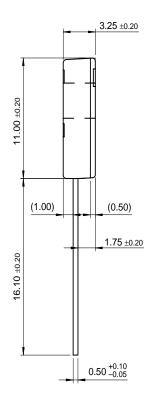
Figure 10. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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